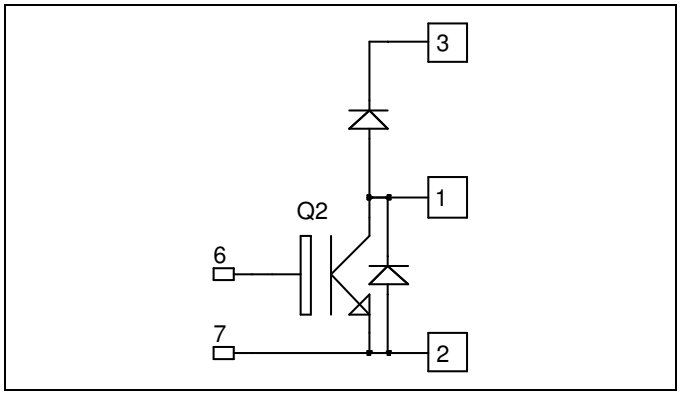
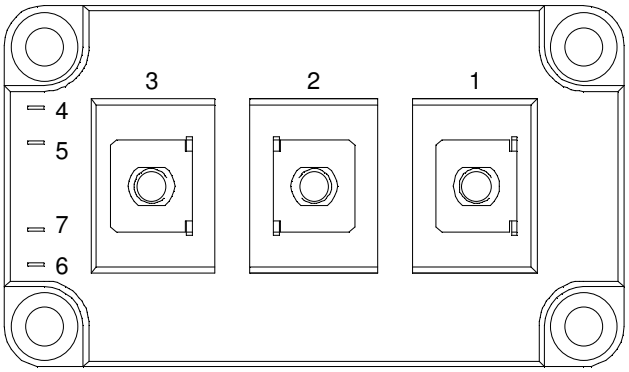
APTGT150DA170D3

Boost chopper
Trench IGBT® Power Module

V_{CES} = 1700V
I_C = 150A @ Tc = 80°C





Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- High level of integration
- Kelvin emitter for easy drive
- Low stray inductance
  - M5 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
I_C	Continuous Collector Current	T_C = 25°C	240	A
		T_C = 80°C	150	
I_{CM}	Pulsed Collector Current	T_C = 25°C	300	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	1040	W
RBSOA	Reverse Bias Safe Operation Area	T_j = 125°C	300A@1700V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
BV_{CES}	Collector - Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 6mA		1700			V
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1700V				10	mA
$V_{CE(on)}$	Collector Emitter on Voltage	V_{GE} = 15V, I_C = 150A	T_j = 25°C		2.0	2.4	V
			T_j = 125°C		2.4		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 6mA		5.2	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				800	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V f = 1MHz		12		nF
C_{res}	Reverse Transfer Capacitance			0.45		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 900V I_C = 150A R_G = 9.1Ω		200		ns
T_r	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			750		
T_f	Fall Time			100		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 900V I_C = 150A R_G = 9.1Ω		230		ns
T_r	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			900		
T_f	Fall Time			200		
E_{off}	Turn Off Energy			50		mJ

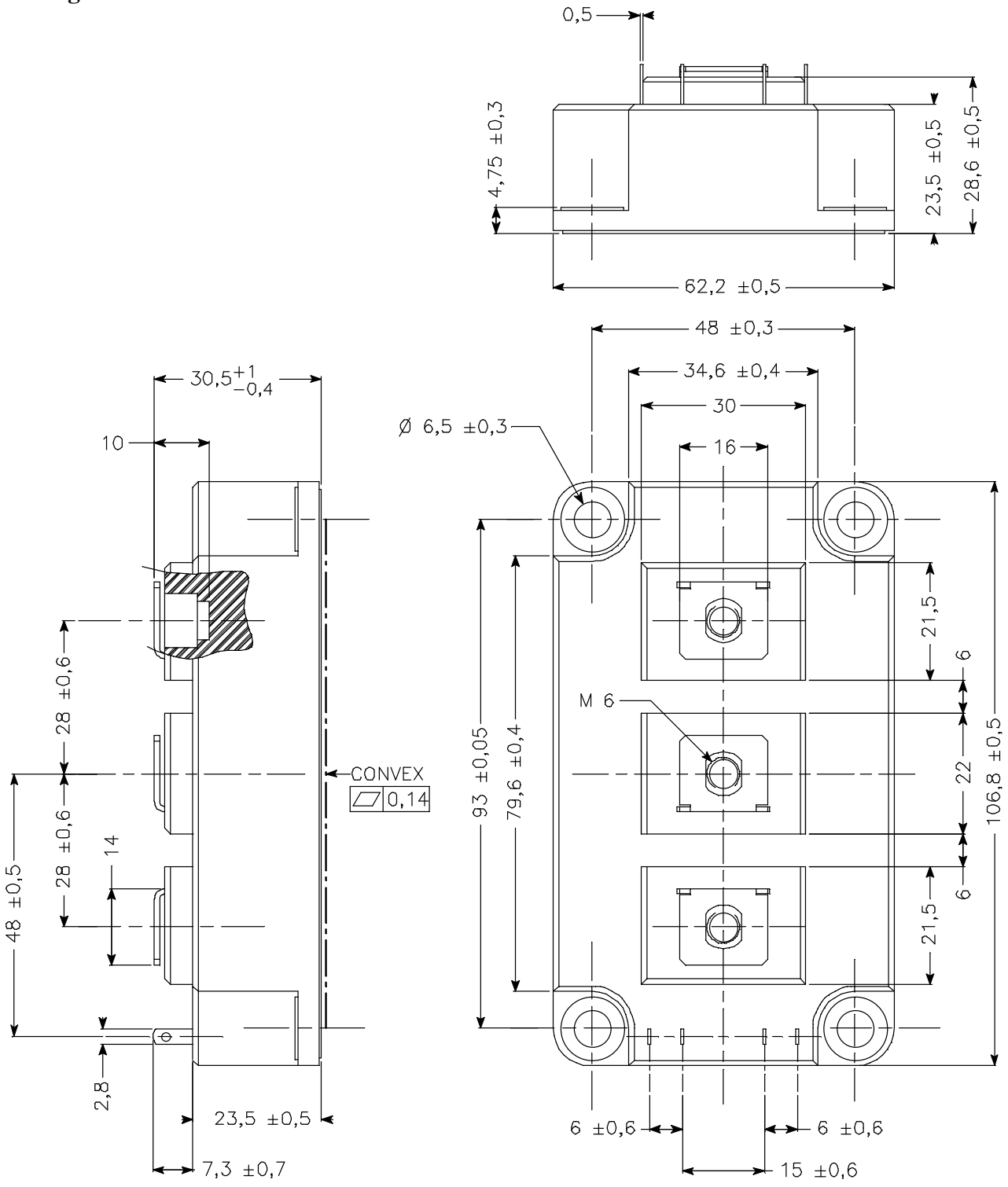
Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_F	Diode Forward Voltage	I_F = 150A V_{GE} = 0V	T_j = 25°C		1.8	2.2	V
			T_j = 125°C		1.9		
E_r	Reverse Recovery Energy	I_F = 150A V_R = 900V di/dt =990A/µs	T_j = 25°C		20		mJ
			T_j = 125°C		35		
Q_{rr}	Reverse Recovery Charge	I_F = 150A V_R = 900V di/dt =990A/µs	T_j = 25°C		40		µC
			T_j = 125°C		65		

Thermal and package characteristics

Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case		IGBT			0.12	°C/W
			Diode			0.21	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	
Wt	Package Weight					380	g

Package outline



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522
5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.